

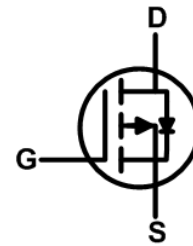


- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

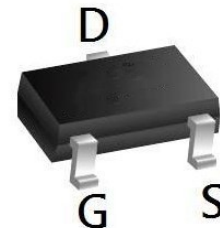
### Description

The WL30P09L is the high cell density trenched P-ch MOSFETs, which provide excellent R<sub>DS(on)</sub> and gate charge for most of the synchronous buck converter applications.

The WL30P09L meet the RoHS and Green Product requirement 100% EAS guaranteed with full function reliability approved.



### SOT23-3L Pin Configuration



### Product Summary

BVDSS	R <sub>DS(on)</sub>	I <sub>D</sub>
-30V	20mΩ	-9.0A

### Absolute Maximum Ratings (T<sub>A</sub>=25°C unless otherwise specified)

Symbol	Parameter	Max.	Units	
V <sub>DSS</sub>	Drain-Source Voltage	-30	V	
V <sub>GSS</sub>	Gate-Source Voltage	±20	V	
I <sub>D</sub>	Continuous Drain Current	T <sub>A</sub> = 25°C	-9	A
		T <sub>A</sub> = 100°C	-5.0	A
I <sub>DM</sub>	Pulsed Drain Current <sup>note1</sup>	-36	A	
E <sub>AS</sub>	Single Pulsed Avalanche Energy <sup>note2</sup>	25	mJ	
P <sub>D</sub>	Power Dissipation	T <sub>A</sub> = 25°C	3.0	W
R <sub>θJA</sub>	Thermal Resistance, Junction to Ambient	48	°C/W	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range	-55 to +150	°C	



**Electrical Characteristics** ( $T_J=25^{\circ}\text{C}$  unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D = -250\mu A$	-30	-	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -30V, V_{GS} = 0V,$	-	-	-1	$\mu A$
$I_{GSS}$	Gate to Body Leakage Current	$V_{DS} = 0V, V_{GS} = \pm 20V$	-	-	$\pm 100$	nA
<b>On Characteristics</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\mu A$	-1.0	-1.5	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>Note3</small>	$V_{GS} = -10V, I_D = -9A$	-	20	25	m $\Omega$
		$V_{GS} = -4.5V, I_D = -5A$	-	27	38	
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = -15V, V_{GS} = 0V,$ $f = 1.0MHz$	-	900	-	pF
$C_{oss}$	Output Capacitance		-	125	-	pF
$C_{rss}$	Reverse Transfer Capacitance		-	109	-	pF
$Q_g$	Total Gate Charge	$V_{DS} = -15V, I_D = -8A,$ $V_{GS} = -10V$	-	42	-	nC
$Q_{gs}$	Gate-Source Charge		-	8.8	-	nC
$Q_{gd}$	Gate-Drain("Miller") Charge		-	7.3	-	nC
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD} = -15V, I_D = -1A,$ $V_{GS} = -10V, R_{GEN} = 6\Omega$	-	13	-	ns
$t_r$	Turn-on Rise Time		-	15	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	198	-	ns
$t_f$	Turn-off Fall Time		-	98	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain to Source Diode Forward Current		-	-	-9	A
$I_{SM}$	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-36	A
$V_{SD}$	Drain to Source Diode Forward Voltage	$V_{GS} = 0V, I_S = -9A$	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition:  $T_J=25^{\circ}\text{C}, V_{DD}=-15V, V_G=-10V, R_G=25\Omega, L=0.5mH, I_{AS}=-10A$

3. Pulse Test: Pulse Width $\leq 300\mu s$ , Duty Cycle $\leq 2\%$



### Typical Performance Characteristics

Figure 1: Output Characteristics

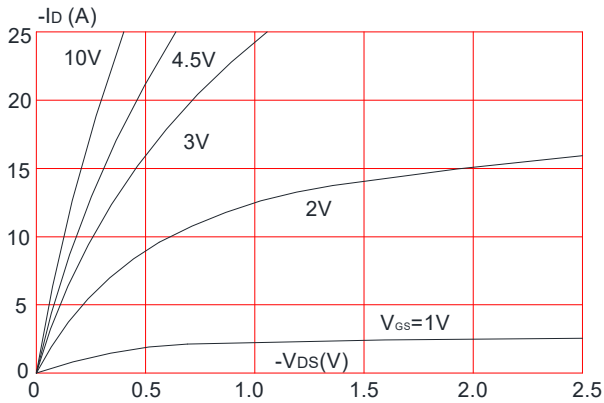


Figure 2: Typical Transfer Characteristics

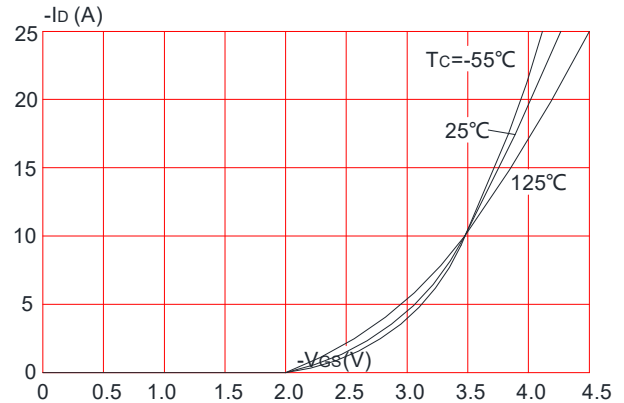


Figure 3: On-resistance vs. Drain Current

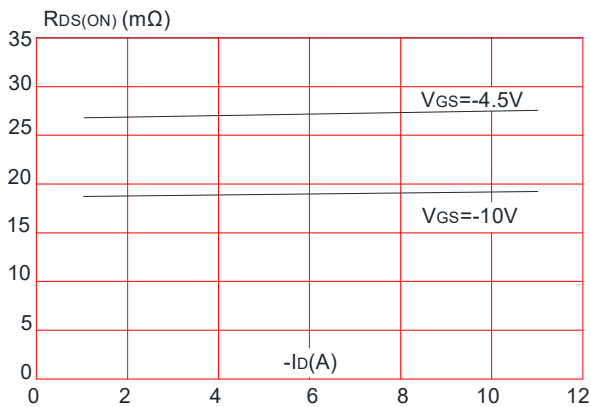


Figure 4: Body Diode Characteristics

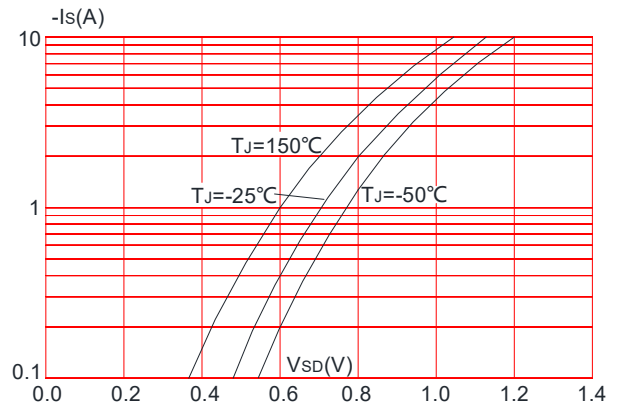


Figure 5: Gate Charge Characteristics

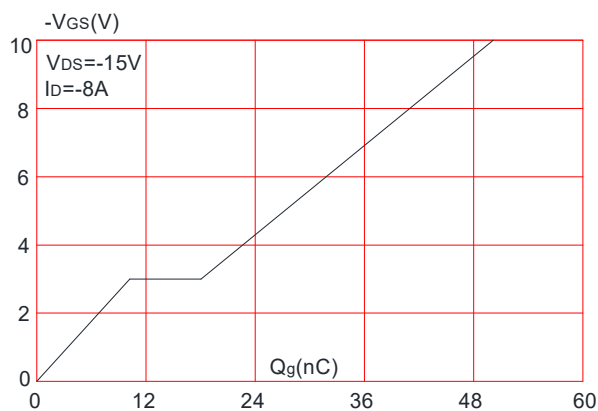
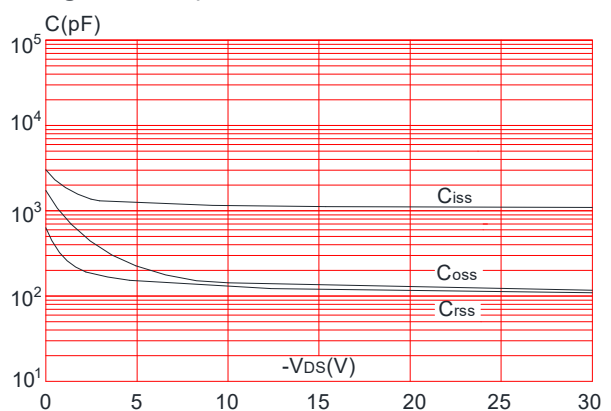
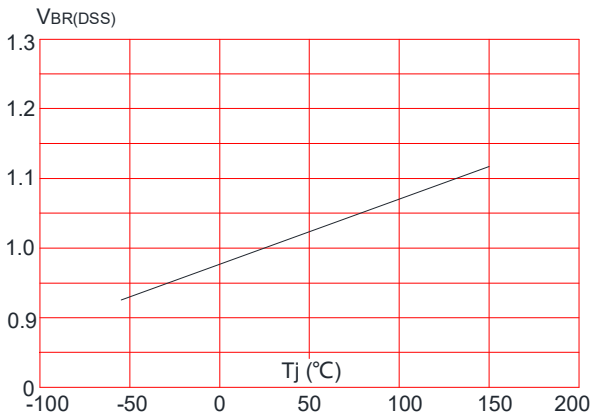


Figure 6: Capacitance Characteristics

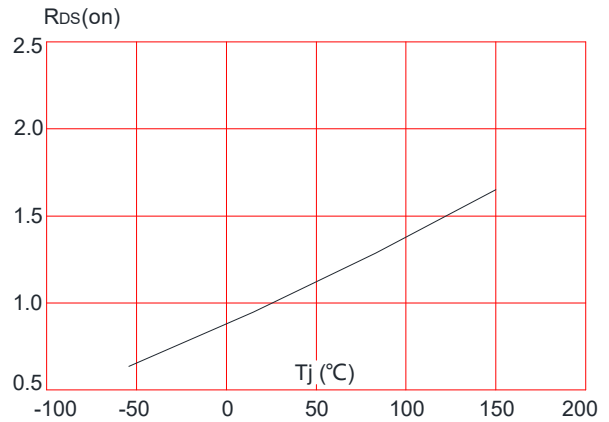




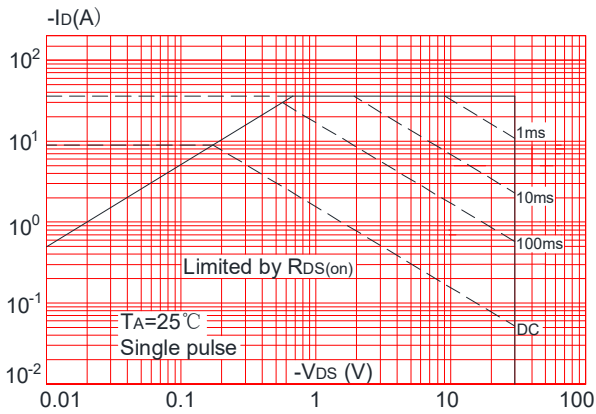
**Figure 7:** Normalized Breakdown Voltage vs. Junction Temperature



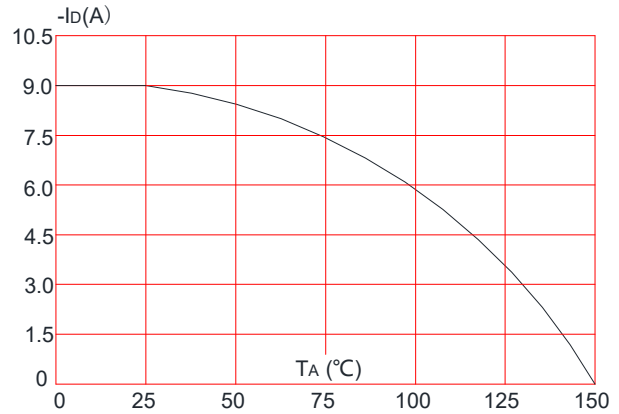
**Figure 8:** Normalized on Resistance vs. Junction Temperature



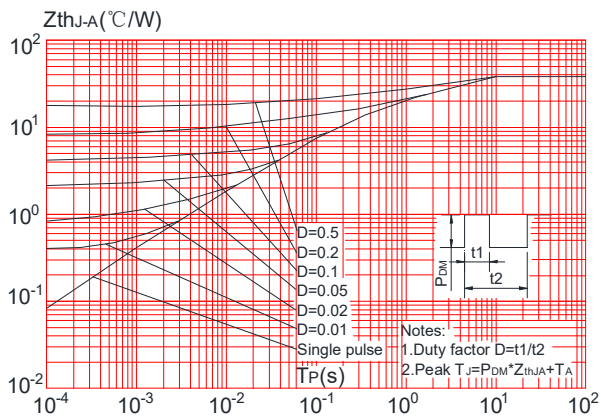
**Figure 9:** Maximum Safe Operating Area



**Figure 10:** Maximum Continuous Drain Current vs. Ambient Temperature



**Figure.11:** Maximum Effective Transient Thermal Impedance, Junction-to-Ambient





### Test Circuit

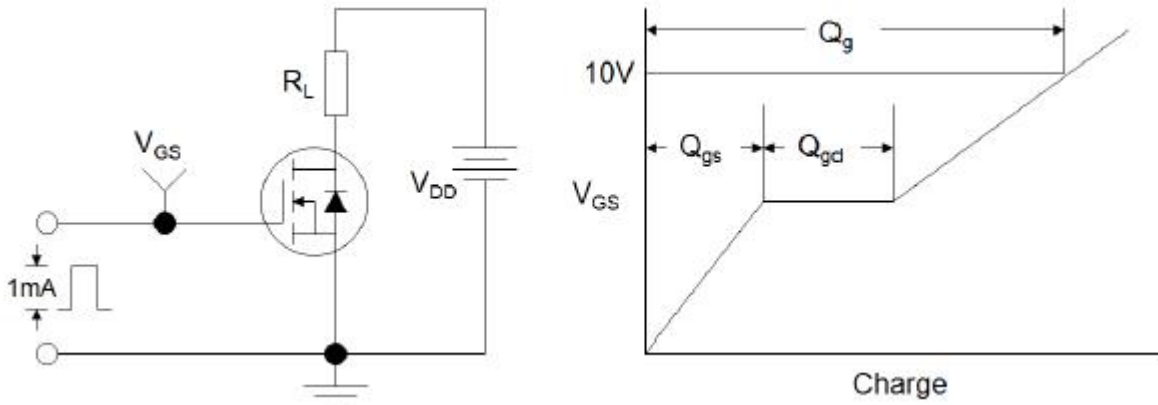


Figure1:Gate Charge Test Circuit & Waveform

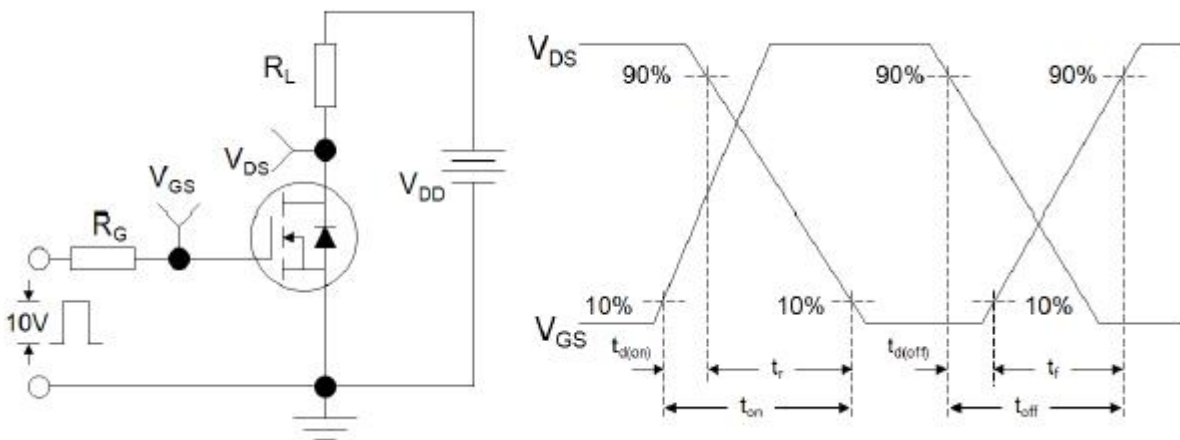


Figure 2: Resistive Switching Test Circuit & Waveforms

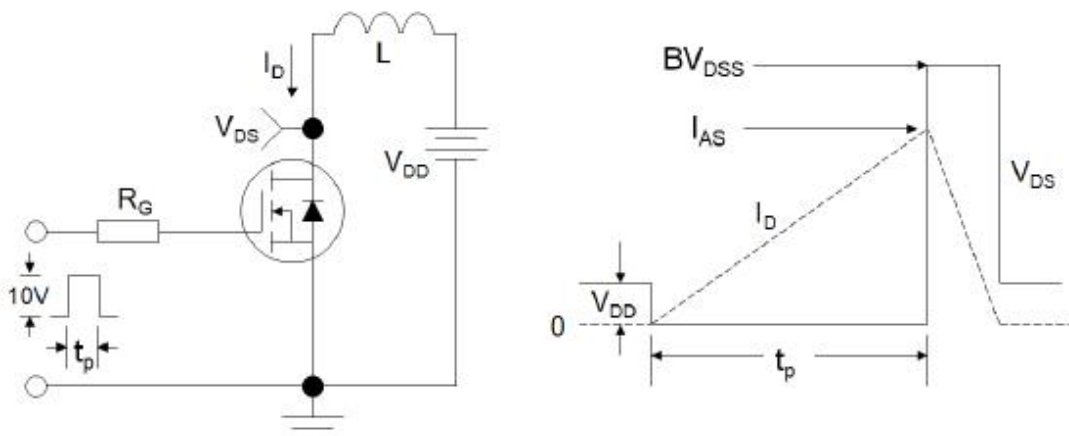
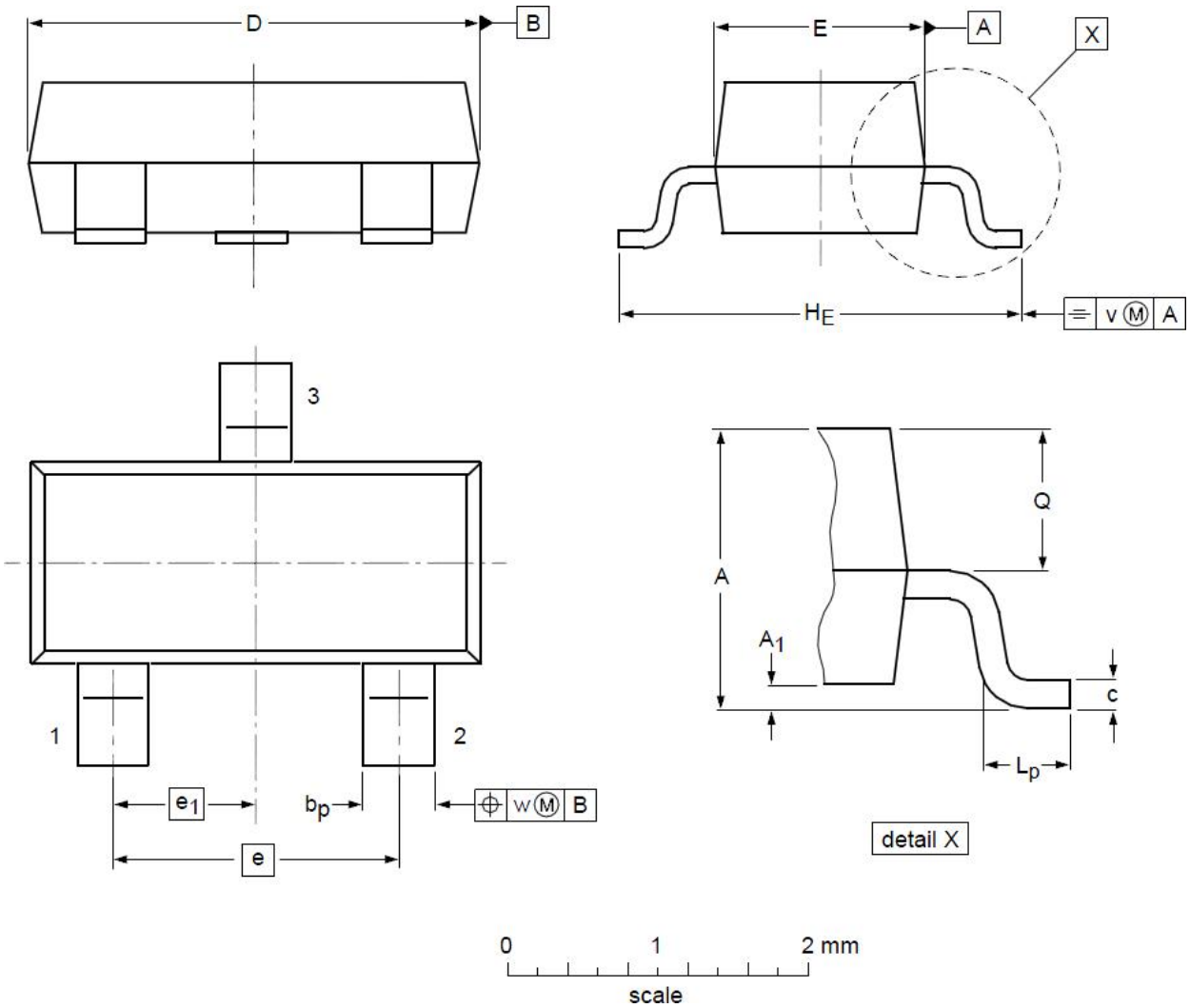


Figure 3:Unclamped Inductive Switching Test Circuit & Waveforms



Package Mechanical Data-SOT-23-3L



DIMENSIONS ( unit : mm )

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.90	1.01	1.15	A <sub>1</sub>	0.01	0.05	0.10
b <sub>p</sub>	0.30	0.42	0.50	c	0.08	0.13	0.15
D	2.80	2.92	3.00	E	1.20	1.33	1.40
e	--	1.90	--	e <sub>1</sub>	--	0.95	--
H <sub>E</sub>	2.25	2.40	2.55	L <sub>p</sub>	0.30	0.42	0.50
Q	0.45	0.49	0.55	v	--	0.20	--
w	--	0.10	--				



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